

EAST: 10615961 ferro mem with non-conductive plug.wsp:1

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(98303) lining liner sidewall side adj wall
(215115) 21.clm.
(22) (17.clm. near3 2.clm.) with 21.clm.
(5) ((17.clm. near3 2.clm.) with 21.clm.) and ((ferr?electric ferr? adj electric ferr?mar
(17) ((17.clm. near3 2.clm.) with 21.clm.) not ((17.clm. near3 2.clm.) with 21.clm.) an
(2) 8485988.pn.
(8888170) after before follow\$4
(1561520) capacit\$4
(8838) ((open\$5 via plug hole)) near9 (after before follow\$4) near9 capacit\$4
(54) (((fet field adj effect adj transistor))
(26361950) (@pd @ad) < "20001117"
(464) 29.clm.
(8) (((fet field adj effect adj transistor))
(35) (((fet field adj effect adj transistor))
(13) (((fet field adj effect adj transistor))
(8) 8174786.URPN
(10) ("5100826" | "5439840" | "5510654" | "5681425" | "5783482" | "584116
(688) (((fet field adj effect adj transistor))
(4) ((ferr?electric ferr? adj electric ferr?magnetic ferr? adj magnetic FeRam FRAM)
(38) (((fet field adj effect adj transistor))
(247316) (lower bottom) adj2 (plate electrode)
(27) (((fet field adj effect adj transistor))

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(((fet field adj effect adj transistor))
(((3mos metal adj oxide) adj transistor) mosfet)
) same (((nonvolatile non adj volatile) adj memory flash eeprom aprom nvram)) and (((open\$5 via plug hole)) near9 (after
before follow\$4) near9 capacit\$4) and ((@pd @ad) < "20001117") (((ferr?electric ferr? adj electric ferr?magnetic ferr? adj
magnetic FeRam FRAM) . ((magnetic adj memory mram) (magnetoresist\$4 magneto adj resist\$4)) (magnetoresist\$4 magneto adj
resist\$4 TMR) (mtj magnetic adj tunnel adj junction)) and (("5100826" | "5439840" | "5510654" | "5681425" | "5783482"
| "5841160" | "5928475" | "5981333" | "5985713" | "6057205".PN.))

May 2004

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	#	+	inventor	Document#	Issue	Pages	Title	Current	Current XR	Retrieval	S	C	P	Image Doc. P
1			Hayashi, Yos	US 6174766	20010:43		Semiconductor device and method of manufa	438/241	257/E21.00		P			US 6174766
2			Jones, Jr., Ro	US 5439840	19950:16		Method of forming a nonvolatile random acc	438/3	257/E27.08		P			US 5439840
3			Asada, Hiroa	US 6859352	20031:28		Semiconductor integrated circuit, a contact	235/482	235/487		P			US 6859352
4			Choi, Kyu Hy	US 6514819	20030:23		High capacity stacked DRAM device and pro	438/253	257/E21.64		P			US 6514819
5			Guedj, Marc	US 6404679	20020:12		Multiple level floating-gate memory	365/185	365/185.03		P			US 6404679
6			Torii, Kazuyo	US 6390574	20020:29		Ferroelectric capacitor with a self-aligned di	257/295	257/310		P			US 6390574
7			Shau, Jeng-J	US 6377484	20020:17		Embedded electrically programmable read on	365/185	365/145		P			US 6377484
8			Nagamine, M	US 6287988	20010:58		Semiconductor device manufacturing metho	438/770	257/E21.19		P			US 6287988
9			Miyamoto, Y	US 6208282	20010:78		A/D converter with input capacitor, feedback	341/158	341/172		P			US 6208282
10			Caywood, Jo	US 6201732	20010:40		Low voltage single CMOS electrically erasab	365/185	257/E27.10		P			US 6201732

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